

ABSTRACT

An electroplating method and an electroplating apparatus relate to the technical field of semiconductor processing. The electroplating method comprises: S10: applying a positive voltage to the central anode, the edge electrode being inactive; S20: acquiring the deposition rate v_1 of the plating layer on the central region, and acquiring the deposition rate v_2 of the plating layer on the edge region; S30: comparing the magnitudes of v_1 and v_2 ; S40: if v_1 is greater than v_2 , applying a positive voltage to the edge electrode, and outputting current I ; S50: if v_1 is smaller than v_2 , applying a negative voltage to the edge electrode, and outputting current I ; S60: if v_1 is equal to v_2 , maintaining the active/inactive state of the edge electrode unchanged. By respectively obtaining the deposition rates of the plating layer on the central region and on the edge region and controlling the voltage and the current of the edge electrode based on the deposition rates, the deposition rate on the edge region can be dynamically adjusted, thereby enabling real-time balancing of the deposition rates between the edge region and the central region and improving the uniformity of electroplating.